

Product Overview

MBRS130LT3G: Schottky Power Rectifier, Surface Mount, 1.0 A, 30 V

For complete documentation, see the data sheet.

The Schottky Rectifier employs the Schottky Barrier principle in a large area metal-to-silicon power diode. The Schottky Rectifier's state-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. It is ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes in surface mount applications where compact size and weight are critical to the system.

Features

- Very Low Forward Voltage Drop (0.395 Volts Max @ 1.0 A, T_J = 25 °C)
- Small Compact Surface Mountable Package with J-Bend Leads
- Highly Stable Oxide Passivated Junction
- Guardring for Stress Protection
- Mechanical Characteristics:
 - Case: Epoxy, Molded
 - Weight: 95 mg (approximately)
 - Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
 - Lead and Mounting Surface Temperature for Soldering Purposes: 260 °C Max. for 10 Seconds
- Shipped in 12 mm Tape and Reel, 2500 units per reel
- Cathode Polarity Band

For more features, see the data sheet

Part Electrical Specifications

Product	Compliance	Status	Configuration	V _{RRM} Min (V)	V _F Max (V)	I _{RM} Max (μA)	I _{O(rec)} Max (A)	I _{FSM} Max (A)	t _r Max (ns)	C _j Max (pF)	Package Type
MBRS130LT3G	Pb-free	Active	Single	30	0.395	1000	1	40	-	-	SMB-2
	Halide free										
SBRS8130LT3G	AEC Qualified	Active	Single	30	0.395	1000	1	40	-	-	SMB-2
	PPAP Capable										
	Pb-free										
	Halide free										

For more information please contact your local sales support at www.onsemi.com.

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